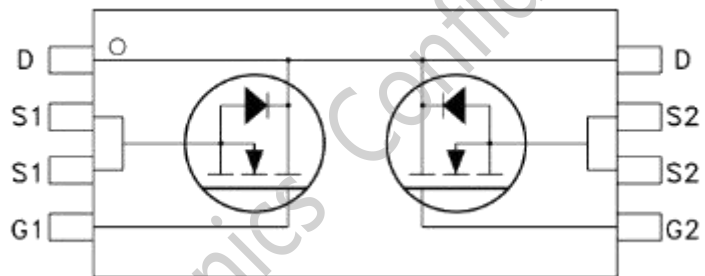
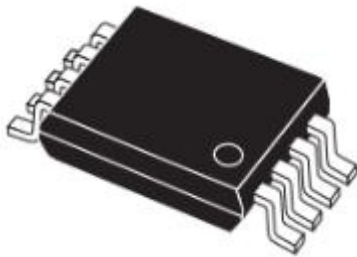


GENERAL DESCRIPTION

DP8205 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

PRODUCT SUMMARY

| | |
|------------------------------------|----------------|
| V_{DS} | 20 V |
| I_D (at $V_{GS}=4.5V$) | 5.0A |
| $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) | < 27m Ω |
| $R_{DS(ON)}$ (at $V_{GS} = 2.5V$) | < 32m Ω |

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Absolute Maximum Ratings $T_A=25^{\circ}C$ unless otherwise noted

| Parameter | Symbol | Limit | Unit |
|--|----------------|------------|-------------|
| Drain-Source Voltage | V_{DS} | 20 | V |
| Gate-Source Voltage | V_{GS} | ± 12 | V |
| Drain Current-Continuous @ $T_J=25^{\circ}C$ | I_D | 5 | A |
| Pulsed ^b | I_{DM} | 20 | A |
| Drain-Source Diode Forward Current ^a | I_S | 2.5 | A |
| Maximum Power Dissipation ^a | P_D | 1.5 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | $^{\circ}C$ |

Thermal Characteristic

| Parameter | Symbol | Limit | Unit |
|--|-----------------|-------|---------------|
| Thermal Resistance, Junction-to-Ambient ^a | $R_{\theta JA}$ | 100 | $^{\circ}C/W$ |

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ ^c | Max | Unit |
|---|--------------|--|---------------|------------------|-----------|------------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 20 | - | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=20V, V_{GS}=0V$ | - | - | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 12V, V_{DS}=0V$ | - | - | ± 100 | nA |
| On Characteristics | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 0.5 | 0.7 | 1.2 | V |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}=4.5V, I_D=4.5A$ | 14 | 20 | 27 | m Ω |
| | | $V_{GS}=2.5V, I_D=3.5A$ | 17 | 26 | 32 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS}=5V, I_D=7A$ | - | 17.7 | - | S |
| Dynamic Characteristics | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=8V,$ $V_{GS}=0V,$ $F=1.0MHz$ | - | 802 | - | pF |
| Output Capacitance | C_{oss} | | - | 153 | - | pF |
| Reverse Transfer Capacitance | C_{rss} | | - | 122 | - | pF |
| Switching Characteristics | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=10V,$ $I_D=1A$ $V_{GS}=4.5V,$ $R_{GEN}=10\Omega,$ $R_L=10\Omega$ | - | 18 | - | nS |
| Turn-on Rise Time | t_r | | - | 5 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 43.8 | - | nS |
| Turn-Off Fall Time | t_f | | - | 20 | - | nS |
| Total Gate Charge | Q_g | | $V_{DS}=10V,$ | - | 10.5 | - |
| Gate-Source Charge | Q_{gs} | $I_D=4A,$ | - | 2 | - | nC |
| Gate-Drain Charge | Q_{gd} | $V_{GS}=4.5V$ | - | 2.5 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage | V_{SD} | $V_{GS}=0V, I_S=1.7A$ | - | - | 1.2 | V |

Notes:

- Surface Mounted on FR4 Board, T < 10 sec ;
- Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- Guaranteed by Design, not subject to production testing.



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

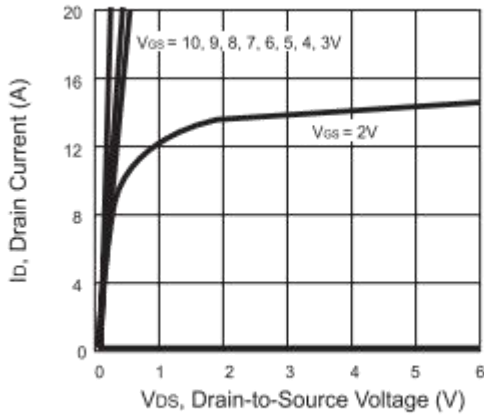


Figure 1. Output Characteristics

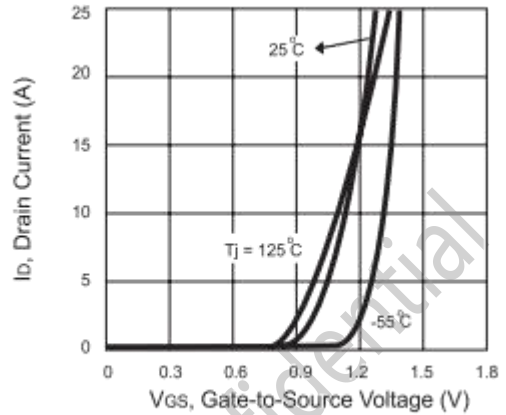


Figure 2. Transfer Characteristics

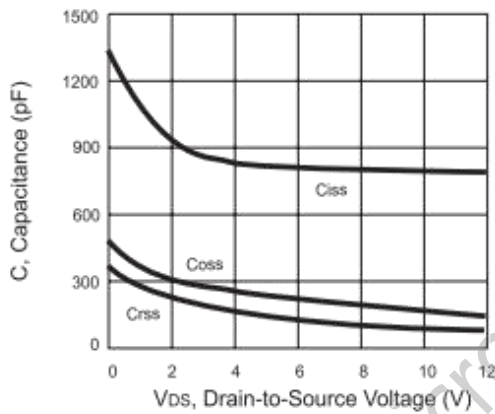


Figure 3. Capacitance

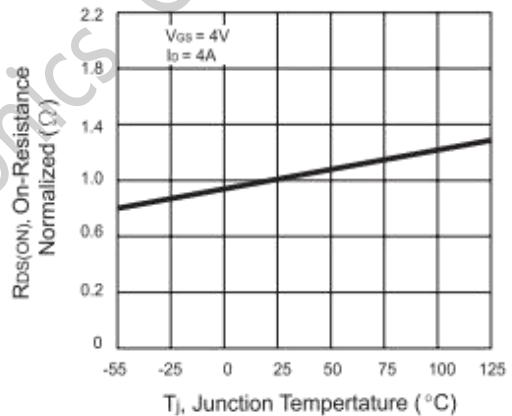


Figure 4. On-Resistance Variation with Temperature

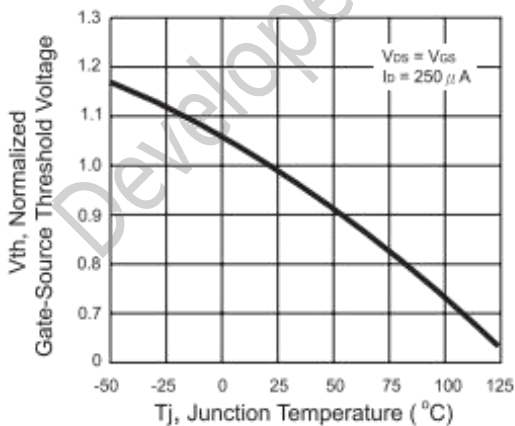


Figure 5. Gate Threshold Variation with Temperature

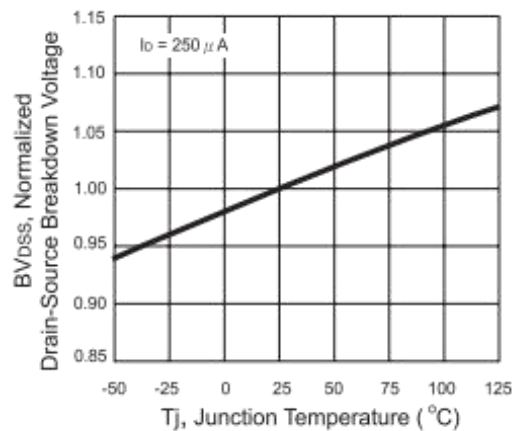


Figure 6. Breakdown Voltage Variation with Temperature

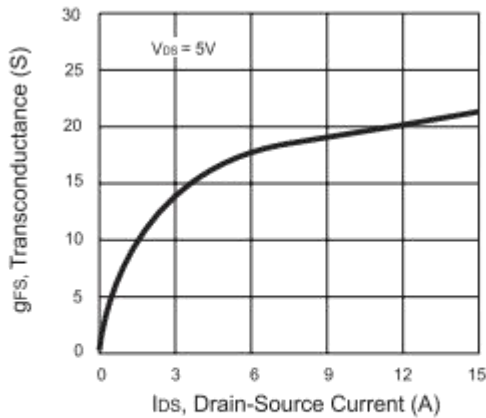


Figure 7. Transconductance Variation with Drain Current

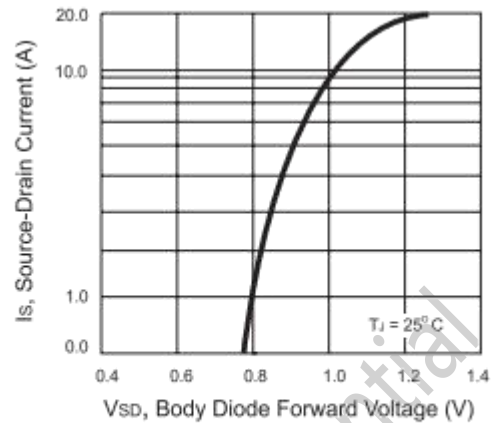


Figure 8. Body Diode Forward Voltage Variation with Source Current

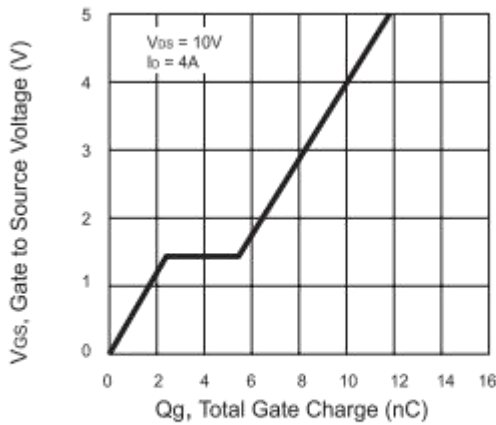


Figure 9. Gate Charge

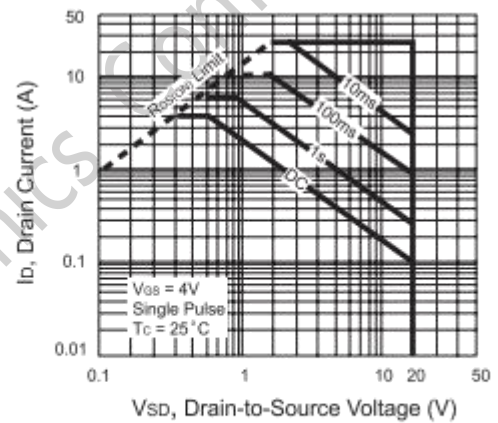


Figure 10. Maximum Safe Operating Area

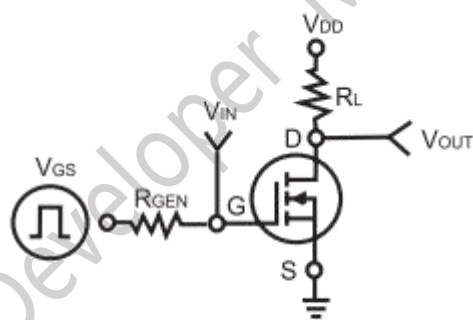


Figure 11. Switching Test Circuit

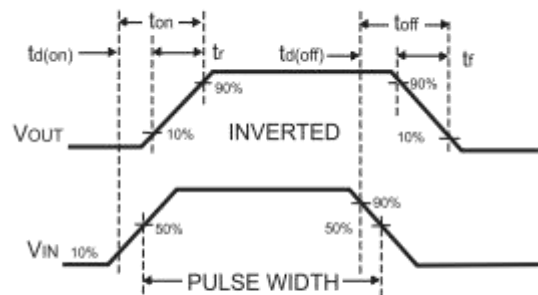
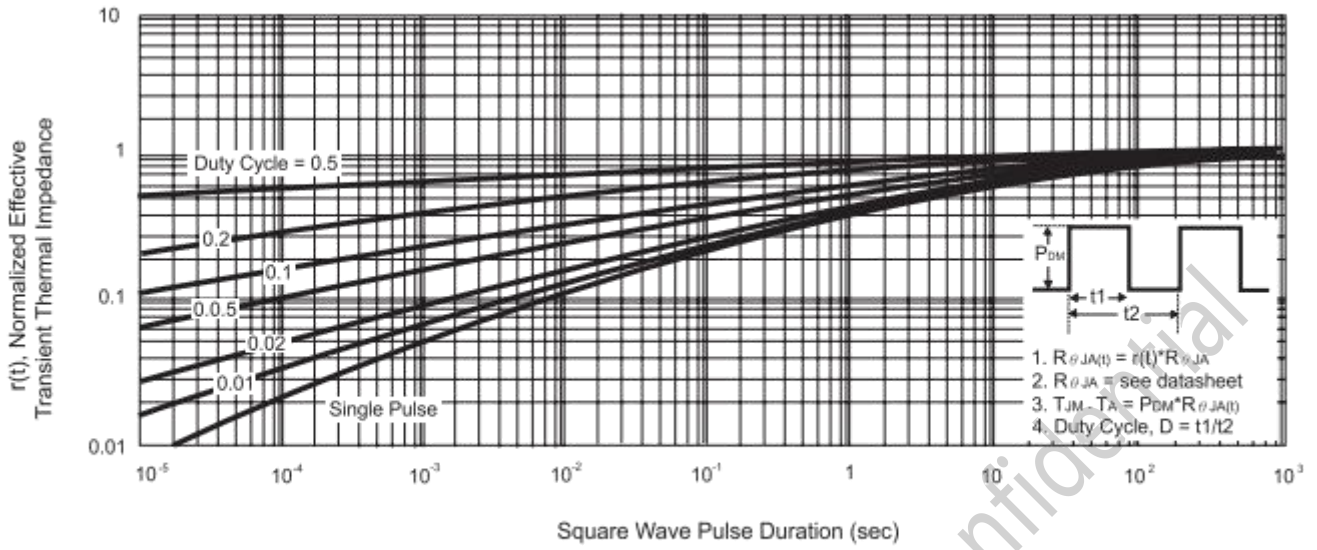
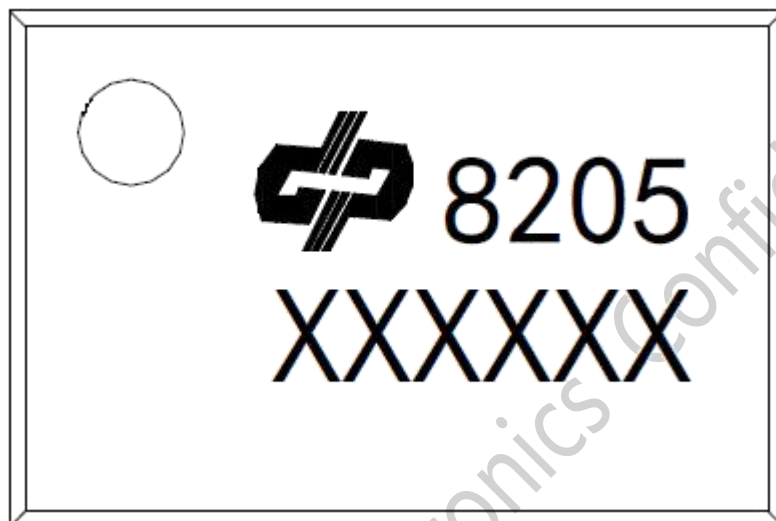


Figure 12. Switching Waveforms



MARKING DESCRIPTION

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NOTE:

Y —Code of productive year code(the last number of the year)

M —Code of productive month(for example: A means January, B means February...)

DD —Productive date(the number of the date)

NN —Lot number of wafer

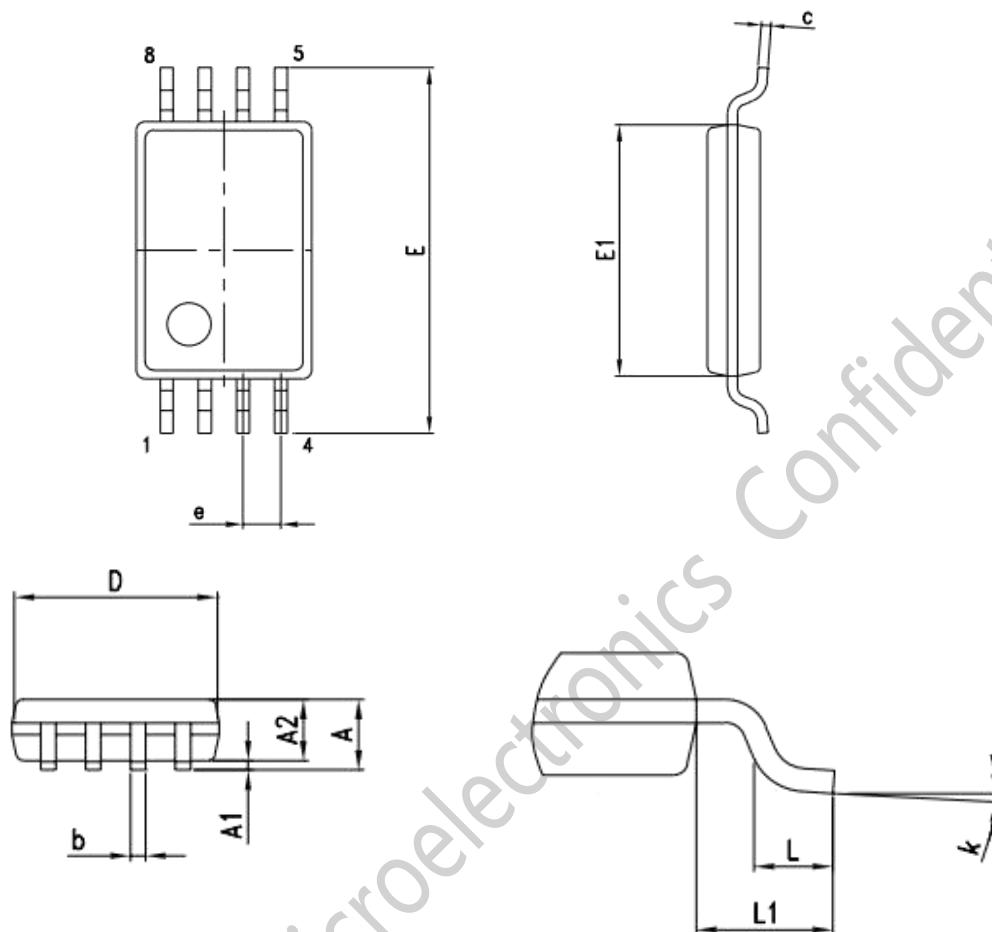
FOR EXCAMPLE:

8E1103

Means this product was produced in 2018-05-11 , and 03 is the wafer lot.

PACKAGE OUTLINE DIMENSIONS

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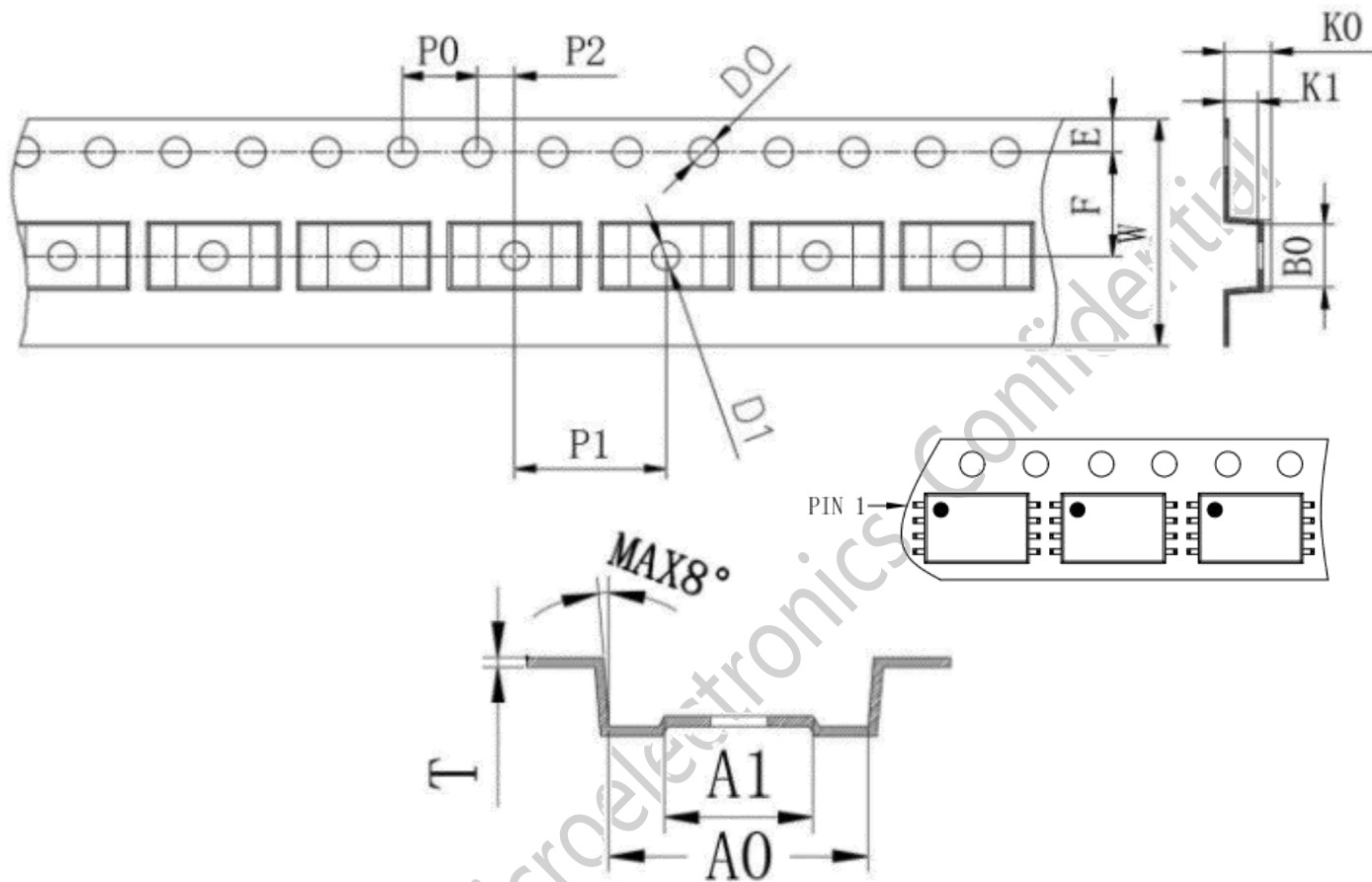


| DIM. | mm. | | | inch. | | |
|------|-------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 1.05 | | 1.20 | 0.041 | | 0.047 |
| A1 | 0.05 | | 0.15 | 0.002 | | 0.006 |
| A2 | 0.80 | | 1.05 | 0.032 | | 0.041 |
| b | 0.19 | | 0.30 | 0.008 | | 0.012 |
| c | 0.090 | | 0.20 | 0.003 | | 0.007 |
| D | 2.90 | | 3.10 | 0.114 | | 0.122 |
| E | 6.20 | | 6.60 | 0.240 | | 0.260 |
| E1 | 4.30 | | 4.50 | 0.170 | | 0.177 |
| e | | 0.65 | | | 0.025 | |
| L | 0.45 | | 0.75 | 0.018 | | 0.030 |
| L1 | | 1.00 | | | 0.039 | |
| k | 0° | | 8° | 0.192 | | 0.208 |



TAPE SIZE

TSSOP8



| | | | | | | |
|--------|-----------|-----------|-----------|-----------|-----------|---|
| SYMBOL | A0 | B0 | K0 | P0 | P1 | P2 |
| SPEC | 6.90±0.10 | 3.30±0.10 | 1.60±0.10 | 4.00±0.10 | 8.00±0.10 | 2.00±0.05 |
| SYMBOL | T | E | F | D0 | D1 | W |
| SPEC | 0.25±0.05 | 1.75±0.10 | 5.50±0.05 | 1.55±0.05 | 1.50±0.10 | 12.00 ^{+0.30} _{-0.10} |

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